

## WHAT IS CLAIMED IS:

1. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:
  - 5 forming an insulating film spacer only on the sidewall of conductive layer patterns at a region where a contact plug will be formed and then forming an interlayer dielectric film on the entire surface.
2. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 1, wherein said conductive layer patterns are word lines or bit lines.
3. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:
  - 15 forming conductive layer patterns of a given pattern and an insulating film spacer on the sidewalls of said conductive layer patterns through a common process;  
removing said insulating film spacer formed in a region other than a region where a contact plug will be formed; and
  - 20 forming an interlayer dielectric film on the entire surface.
4. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 3, wherein said conductive layer patterns are word lines or bit lines.

5. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:

forming conductive layer patterns of a given pattern through a common  
5 process;

forming an interlayer dielectric film on the entire surface; and

removing said interlayer dielectric film at a region where a contact plug will be formed and then forming an insulating film spacer on the sidewall of said conductive layer patterns.

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6. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 5, wherein said conductive layer patterns are word lines or bit line.

15 7. A method of forming an interlayer dielectric film in a semiconductor device, comprising the steps of:

forming conductive layer patterns of a given pattern and an insulating film spacer on the sidewall of said conductive layer patterns through a common process;

20 burying a conductive material between said conductive layer patterns;

removing said conductive material only at a given region and remaining said conductive material at remaining regions to form a contact plug; and

burying an interlayer dielectric film between said conductive layer

patterns at a region from which said conductive material is removed.

8. The method of forming an interlayer dielectric film in a semiconductor device as claimed in claim 7, wherein said conductive layer patterns are word  
5 lines or bit lines.